

# FDD6796A / FDU6796A\_F071

## N-Channel PowerTrench® MOSFET

25 V, 5.7 mΩ

### Features

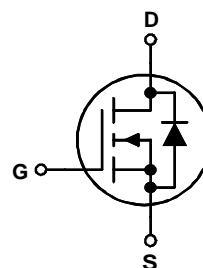
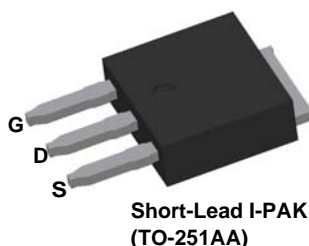
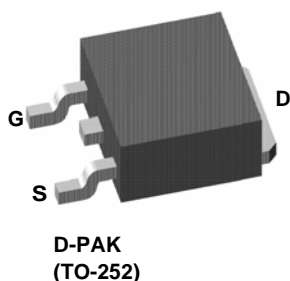
- Max  $r_{DS(on)}$  = 5.7 mΩ at  $V_{GS} = 10\text{ V}$ ,  $I_D = 20\text{ A}$
- Max  $r_{DS(on)}$  = 15.0 mΩ at  $V_{GS} = 4.5\text{ V}$ ,  $I_D = 15.2\text{ A}$
- 100% UIL tested
- RoHS Compliant

### General Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low  $r_{DS(on)}$  and fast switching speed.

### Applications

- Vcore DC-DC for Desktop Computers and Servers
- VRM for Intermediate Bus Architecture



### MOSFET Maximum Ratings $T_C = 25\text{ °C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain to Source Voltage	25	V
$V_{GS}$	Gate to Source Voltage	±20	V
$I_D$	Drain Current -Continuous (Package limited) $T_C = 25\text{ °C}$	40	A
	-Continuous (Silicon limited) $T_C = 25\text{ °C}$	67	
	-Continuous $T_A = 25\text{ °C}$ (Note 1a)	20	
	-Pulsed	150	
$E_{AS}$	Single Pulse Avalanche Energy (Note 3)	40	mJ
$P_D$	Power Dissipation $T_C = 25\text{ °C}$	42	W
	Power Dissipation $T_A = 25\text{ °C}$ (Note 1a)	3.7	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +175	°C

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.6	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	40	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD6796A	FDD6796A	D-PAK (TO-252)	13 "	12 mm	2500 units
FDU6796A	FDU6796A_F071	TO-251AA	N/A(Tube)	N/A	75 units

**Electrical Characteristics**  $T_J = 25\text{ }^{\circ}\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$ , $V_{GS} = 0\text{ V}$	25			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^{\circ}\text{C}$		16		mV/ $^{\circ}\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 20\text{ V}$ , $V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{ V}$ , $V_{DS} = 0\text{ V}$			$\pm 100$	nA

**On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\text{ }\mu\text{A}$	1.0	1.9	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^{\circ}\text{C}$		-6		mV/ $^{\circ}\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}$ , $I_D = 20\text{ A}$		4.3	5.7	m $\Omega$
		$V_{GS} = 4.5\text{ V}$ , $I_D = 15.2\text{ A}$		11.1	15.0	
		$V_{GS} = 10\text{ V}$ , $I_D = 20\text{ A}$ , $T_J = 150\text{ }^{\circ}\text{C}$		6.5	8.6	
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{ V}$ , $I_D = 20\text{ A}$		118		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 13\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$		1336	1780	pF
$C_{oss}$	Output Capacitance			298	400	pF
$C_{rss}$	Reverse Transfer Capacitance			266	400	pF
$R_g$	Gate Resistance			1.2		$\Omega$

**Switching Characteristics**

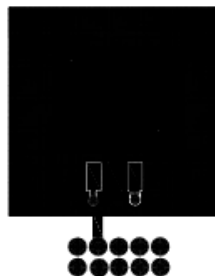
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 13\text{ V}$ , $I_D = 20\text{ A}$ , $V_{GS} = 10\text{ V}$ , $R_{GEN} = 6\text{ }\Omega$		8	16	ns
$t_r$	Rise Time			7	14	ns
$t_{d(off)}$	Turn-Off Delay Time			19	34	ns
$t_f$	Fall Time			4	10	ns
$Q_g$	Total Gate Charge	$V_{GS} = 0\text{ V}$ to $10\text{ V}$	$V_{DD} = 13\text{ V}$ , $I_D = 20\text{ A}$	24	34	nC
$Q_g$	Total Gate Charge	$V_{GS} = 0\text{ V}$ to $5\text{ V}$		14	20	nC
$Q_{gs}$	Gate to Source Charge			4.0		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			5.7		nC

**Drain-Source Diode Characteristics**

$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$ , $I_S = 3.1\text{ A}$ (Note 2)		0.8	1.2	V
		$V_{GS} = 0\text{ V}$ , $I_S = 20\text{ A}$ (Note 2)		0.9	1.3	
$t_{rr}$	Reverse Recovery Time	$I_F = 20\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$		15	27	ns
$Q_{rr}$	Reverse Recovery Charge			4	10	nC

**Notes:**

1:  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  
 $R_{\theta JC}$  is guaranteed by design while  $R_{\theta JA}$  is determined by the user's board design.



a)  $40\text{ }^{\circ}\text{C}/\text{W}$  when mounted on a  
1 in<sup>2</sup> pad of 2 oz copper



b)  $96\text{ }^{\circ}\text{C}/\text{W}$  when mounted on  
a minimum pad

2: Pulse Test: Pulse Width < 300  $\mu\text{s}$ , Duty cycle < 2.0%.

3:  $E_{AS}$  of 40 mJ is based on starting  $T_J = 25\text{ }^{\circ}\text{C}$ ,  $L = 1\text{ mH}$ ,  $I_{AS} = 9\text{ A}$ ,  $V_{DD} = 23\text{ V}$ ,  $V_{GS} = 10\text{ V}$ . 100% test at  $L = 0.1\text{ mH}$ ,  $I_{AS} = 21\text{ A}$ .

## Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

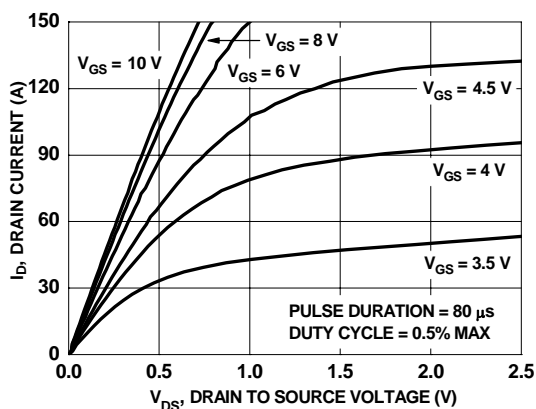


Figure 1. On Region Characteristics

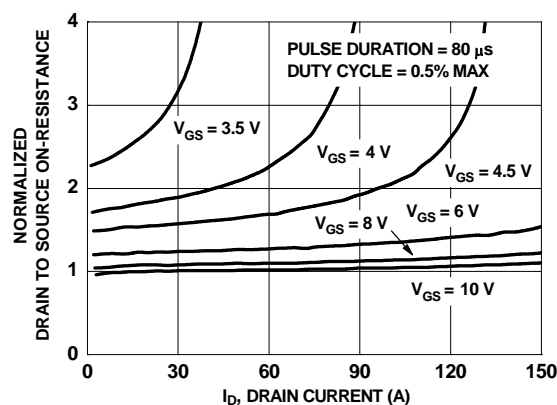


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

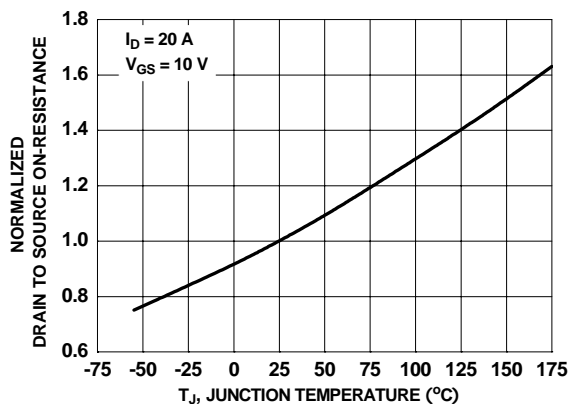


Figure 3. Normalized On Resistance vs Junction Temperature

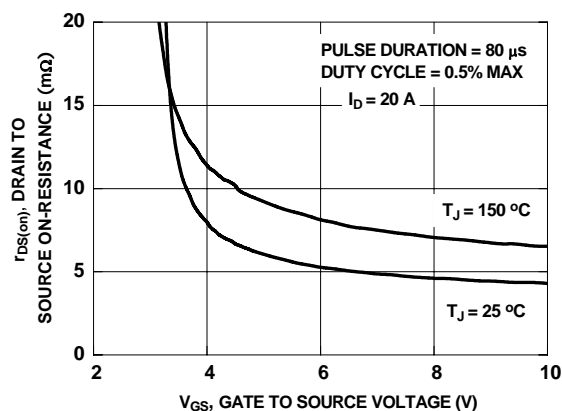


Figure 4. On-Resistance vs Gate to Source Voltage

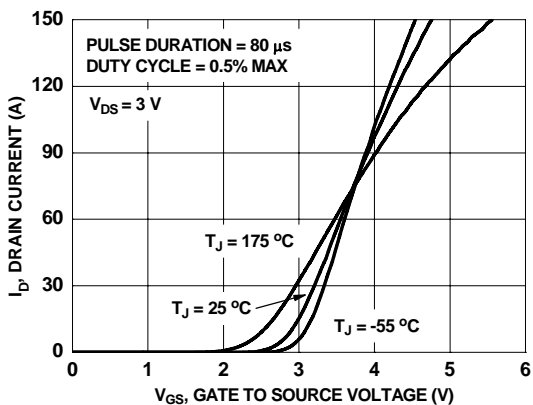


Figure 5. Transfer Characteristics

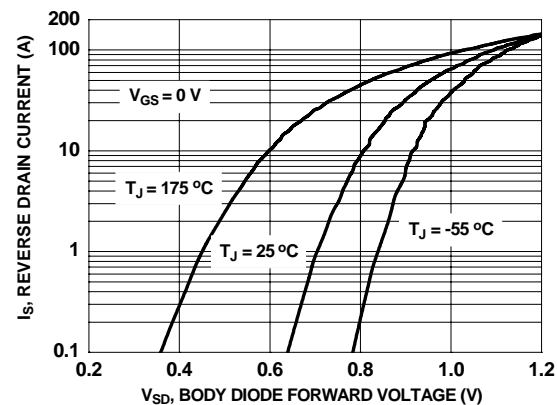


Figure 6. Source to Drain Diode Forward Voltage vs Source Current